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Kind regards,

Team Nexperia

# DATA SHEET



## **PRL5817; PRL5818; PRL5819** Schottky barrier diodes

Product data sheet  
Supersedes data of 1996 May 03

1999 Apr 22

## Schottky barrier diodes

**PRLL5817; PRLL5818;  
PRLL5819**

### FEATURES

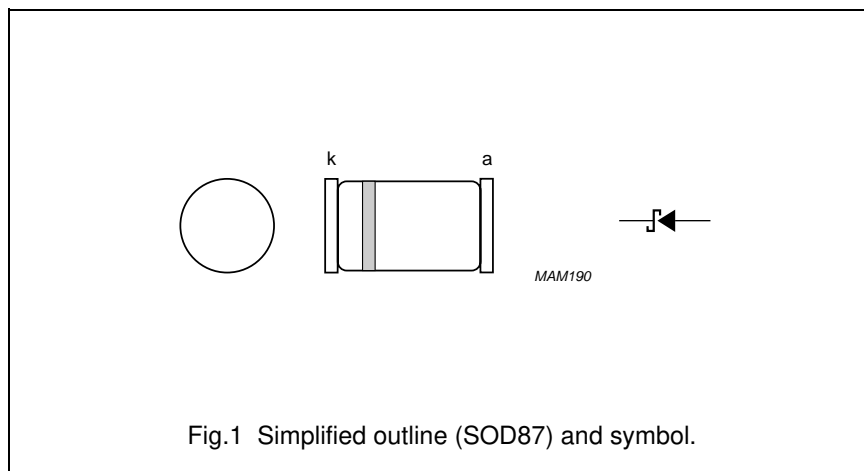
- Low switching losses
- Fast recovery time
- Guard ring protected
- Hermetically sealed glass SMD package.

### APPLICATIONS

- Low power, switched-mode power supplies
- Rectifying
- Polarity protection.

### DESCRIPTION

The PRLL5817 to PRLL5819 types are Schottky barrier diodes fabricated in planar technology, and encapsulated in SOD87 hermetically sealed glass SMD packages incorporating Implotec<sup>TM(1)</sup> technology.



### MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PRLL5817    | 9            |
| PRLL5818    | 9            |
| PRLL5819    | 9            |

(1) Implotec is a trademark of Philips.

## Schottky barrier diodes

PRLL5817; PRLL5818;  
PRLL5819**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL             | PARAMETER                           | CONDITIONS  | MIN. | MAX. | UNIT |
|--------------------|-------------------------------------|---|------|------|------|
| V <sub>R</sub>     | continuous reverse voltage          |   |      |      |      |
|                    | PRLL5817                            |   | –    | 20   | V    |
|                    | PRLL5818                            |   | –    | 30   | V    |
|                    | PRLL5819                            |   | –    | 40   | V    |
| V <sub>RSM</sub>   | non-repetitive peak reverse voltage |   |      |      |      |
|                    | PRLL5817                            |   | –    | 24   | V    |
|                    | PRLL5818                            |   | –    | 36   | V    |
|                    | PRLL5819                            |   | –    | 48   | V    |
| V <sub>RRM</sub>   | repetitive peak reverse voltage     |   |      |      |      |
|                    | PRLL5817                            |   | –    | 20   | V    |
|                    | PRLL5818                            |   | –    | 30   | V    |
|                    | PRLL5819                            |   | –    | 40   | V    |
| V <sub>RWM</sub>   | crest working reverse voltage       |   |      |      |      |
|                    | PRLL5817                            |   | –    | 20   | V    |
|                    | PRLL5818                            |   | –    | 30   | V    |
|                    | PRLL5819                            |   | –    | 40   | V    |
| I <sub>F(AV)</sub> | average forward current             | T <sub>amb</sub> = 60 °C  | –    | 1    | A    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | t = 10 ms half sine wave;<br>T <sub>j</sub> = T <sub>j max</sub> prior to surge: V <sub>R</sub> = 0 | –    | 25   | A    |
| T <sub>stg</sub>   | storage temperature                 |   | –65  | +175 | °C   |
| T <sub>j</sub>     | junction temperature                |   | –    | 125  | °C   |

## Schottky barrier diodes

PRLL5817; PRLL5818;  
PRLL5819**ELECTRICAL CHARACTERISTICS**T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL         | PARAMETER   | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|----------------|---|--|------|------|------|------|
| V <sub>F</sub> | forward voltage<br>PRLL5817                           | see Fig.2  |      |      |      |      |
|                |   | I <sub>F</sub> = 0.1 A   | –    | –    | 320  | mV   |
|                |   | I <sub>F</sub> = 1 A   | –    | –    | 450  | mV   |
|                |   | I <sub>F</sub> = 3 A   | –    | –    | 750  | mV   |
| V <sub>F</sub> | forward voltage<br>PRLL5818                           | see Fig.2  |      |      |      |      |
|                |   | I <sub>F</sub> = 0.1 A   | –    | –    | 330  | mV   |
|                |   | I <sub>F</sub> = 1 A   | –    | –    | 550  | mV   |
|                |   | I <sub>F</sub> = 3 A   | –    | –    | 875  | mV   |
| V <sub>F</sub> | forward voltage<br>PRLL5819                           | see Fig.2  |      |      |      |      |
|                |   | I <sub>F</sub> = 0.1 A   | –    | –    | 340  | mV   |
|                |   | I <sub>F</sub> = 1 A   | –    | –    | 600  | mV   |
|                |   | I <sub>F</sub> = 3 A   | –    | –    | 900  | mV   |
| I <sub>R</sub> | reverse current                                       | V <sub>R</sub> = V <sub>RRMmax</sub> ; note 1                  | –    | 0.5  | 1    | mA   |
|                |   | V <sub>R</sub> = V <sub>RRMmax</sub> ; T <sub>j</sub> = 100 °C | –    | 5    | 10   | mA   |
| C <sub>d</sub> | diode capacitance<br>PRLL5817<br>PRLL5818<br>PRLL5819 | V <sub>R</sub> = 4 V; f = 1 MHz                                |      |      |      |      |
|                |   |  | –    | 70   | –    | pF   |
|                |   |  | –    | 50   | –    | pF   |
|                |   |  | –    | 50   | –    | pF   |

**Note**1. Pulse test: t<sub>p</sub> = 300 μs; δ = 0.02.**THERMAL CHARACTERISTICS**

| SYMBOL              | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | note 1     | 150   | K/W  |

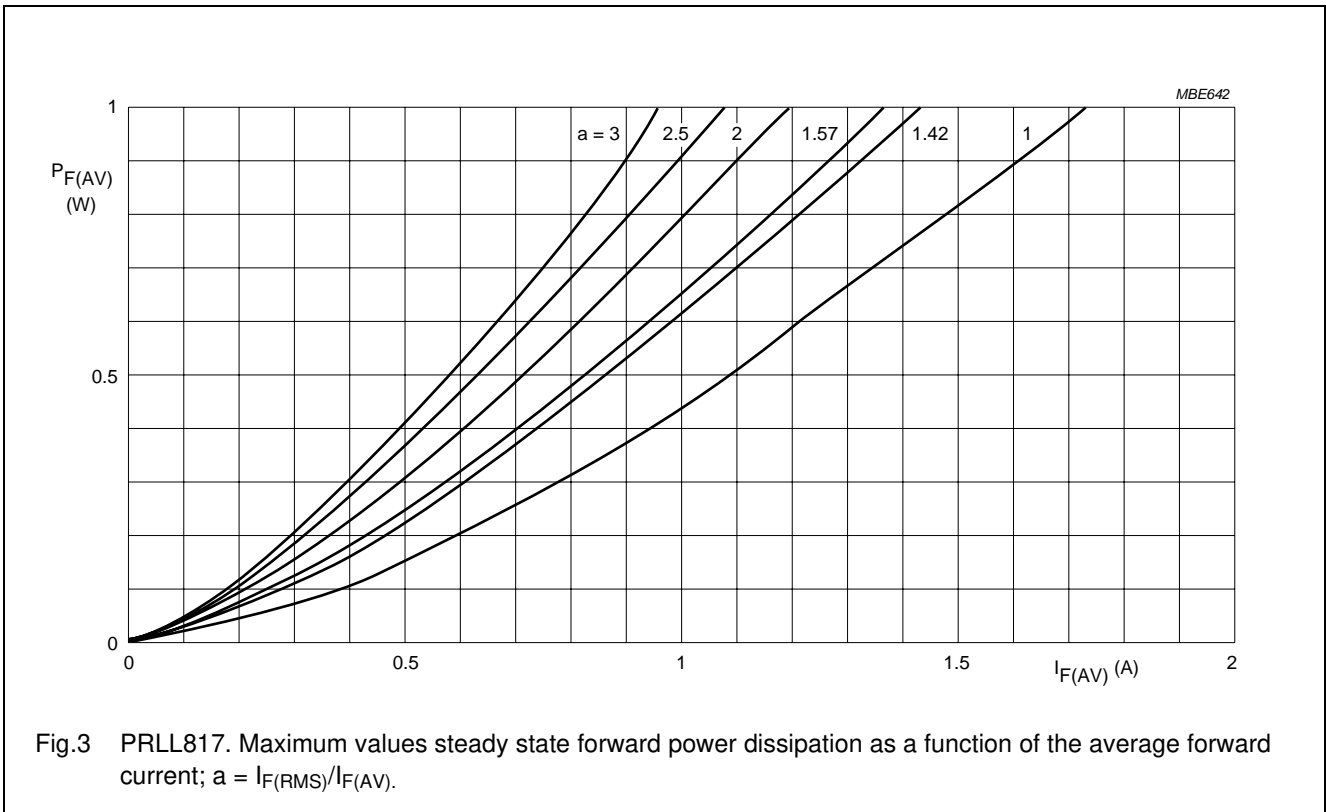
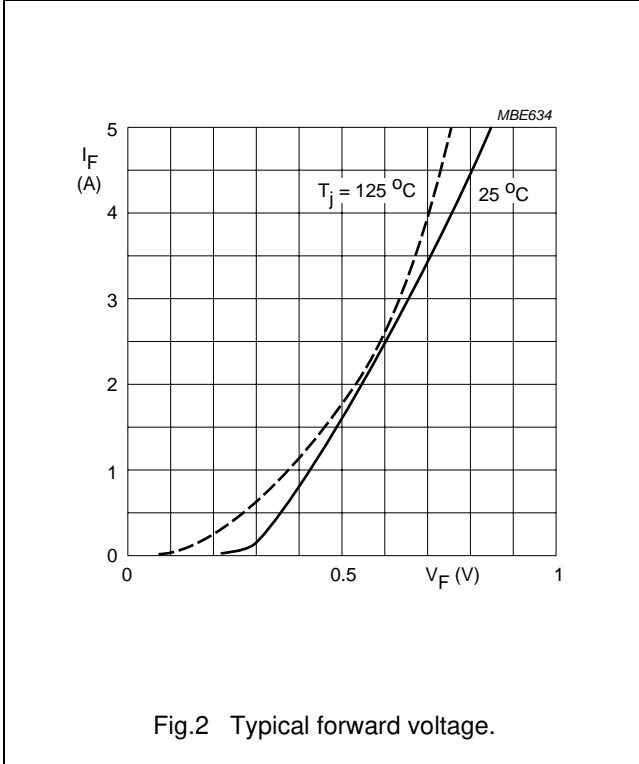
**Note**

1. Refer to SOD87 standard mounting conditions.

# Schottky barrier diodes

PRLL5817; PRLL5818;  
PRLL5819

## GRAPHICAL DATA



Schottky barrier diodes

PRLL5817; PRLL5818;  
PRLL5819

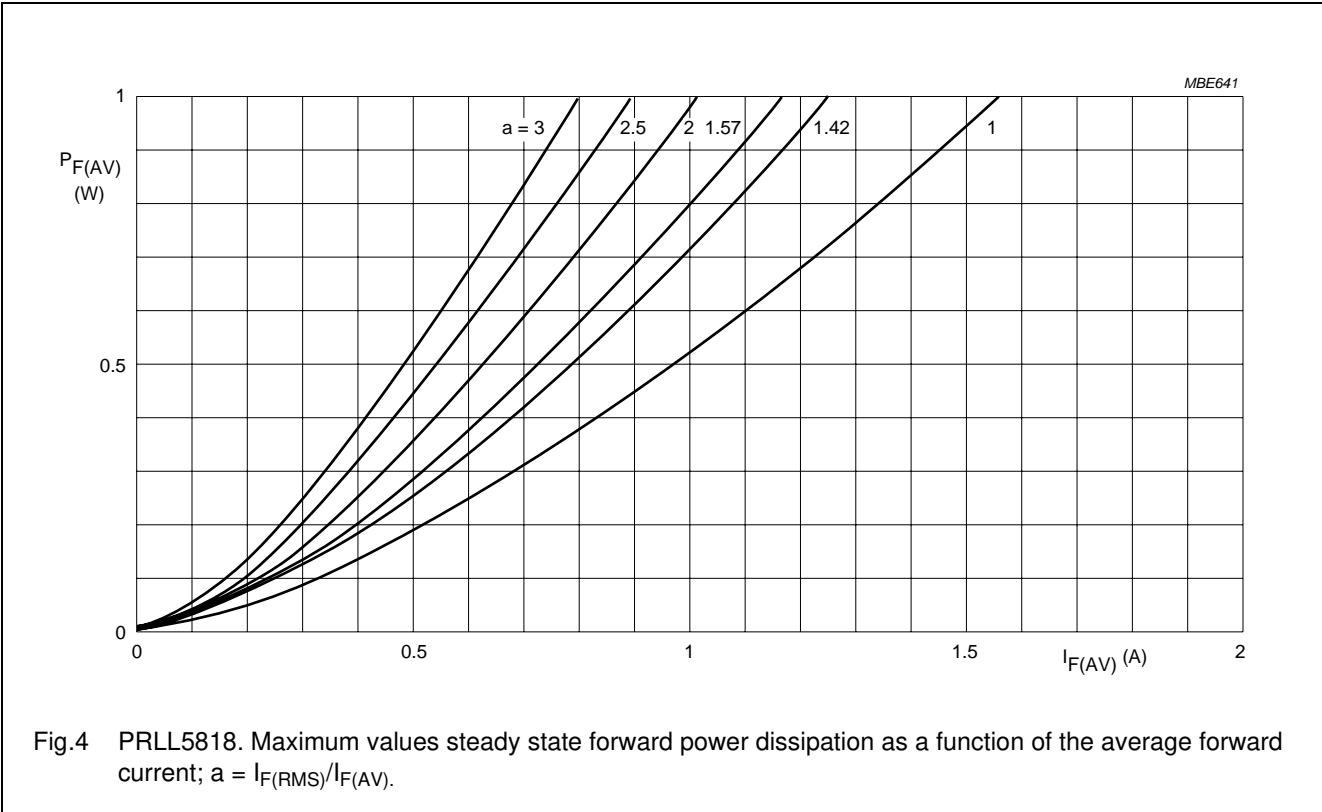


Fig.4 PRLL5818. Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(RMS)}/I_{F(AV)}$ .

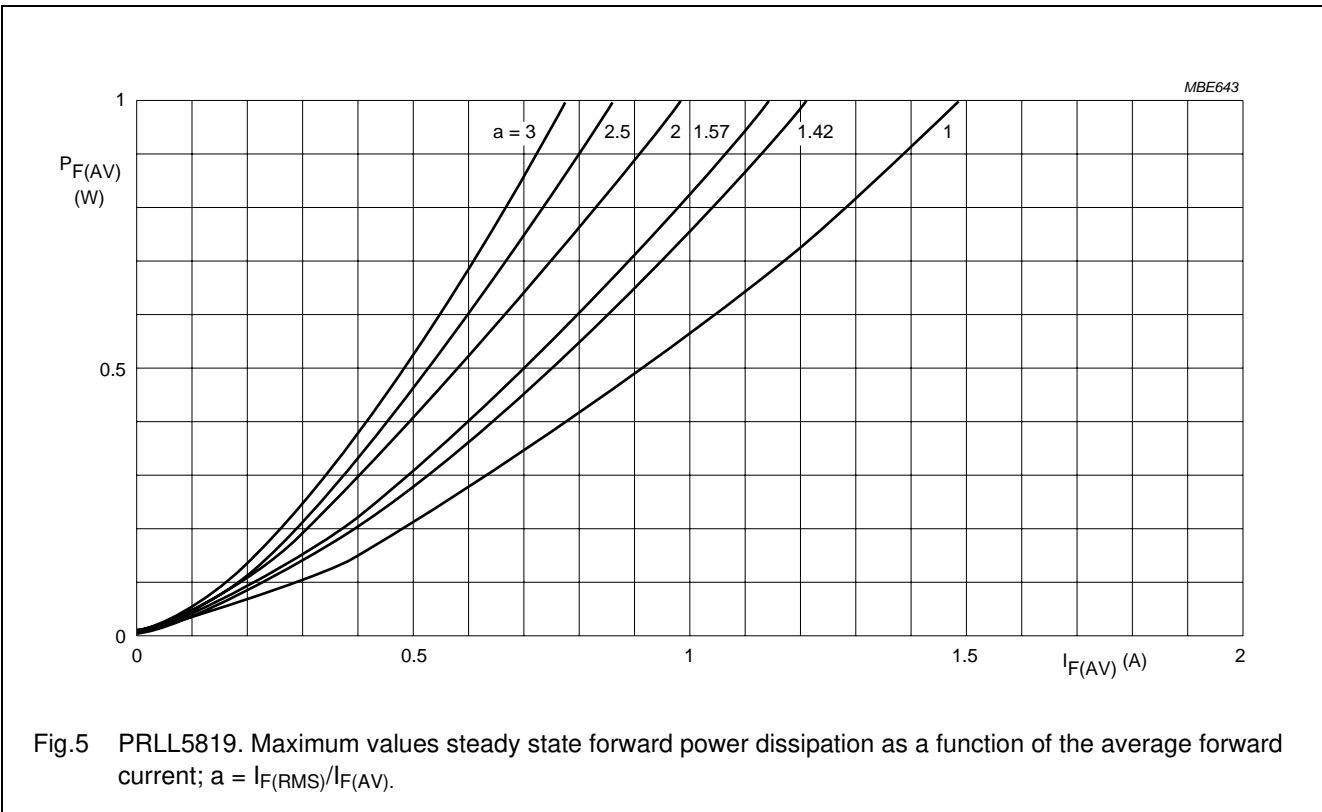
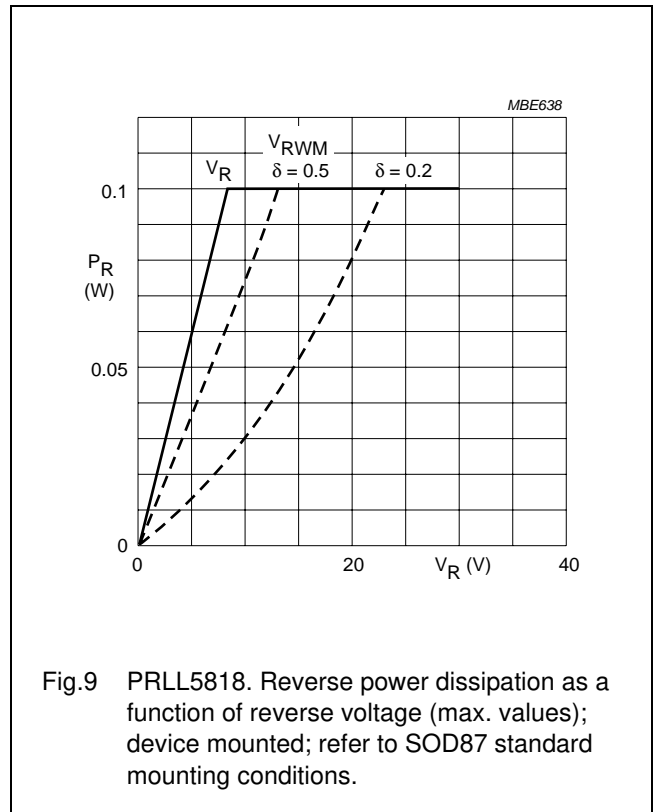
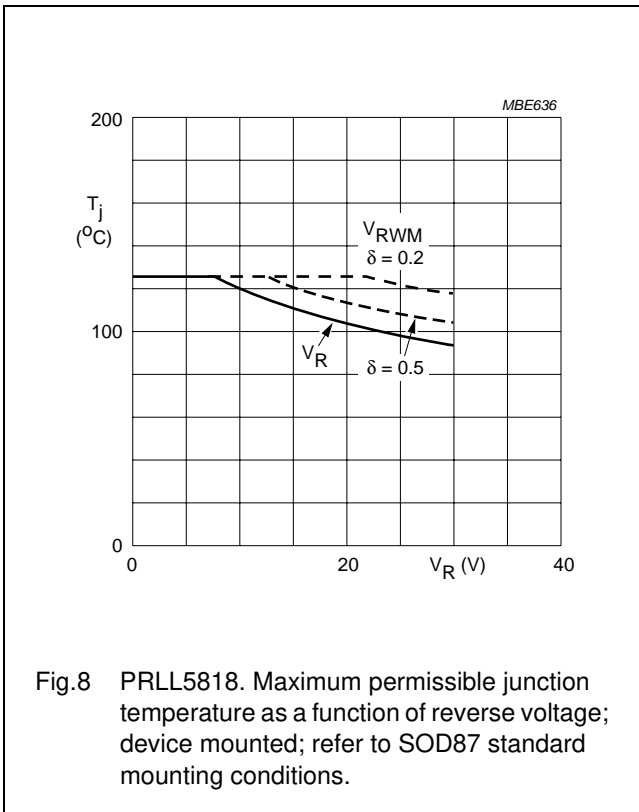
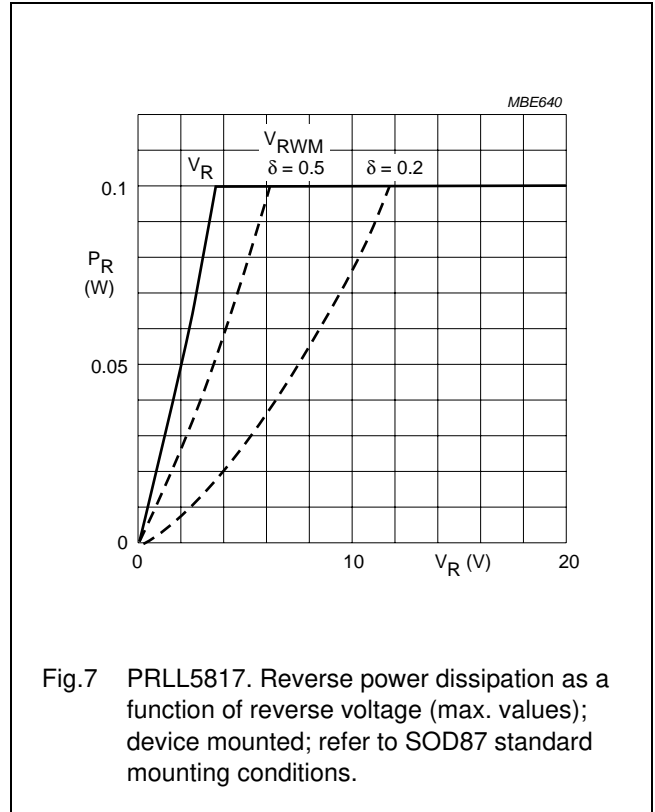
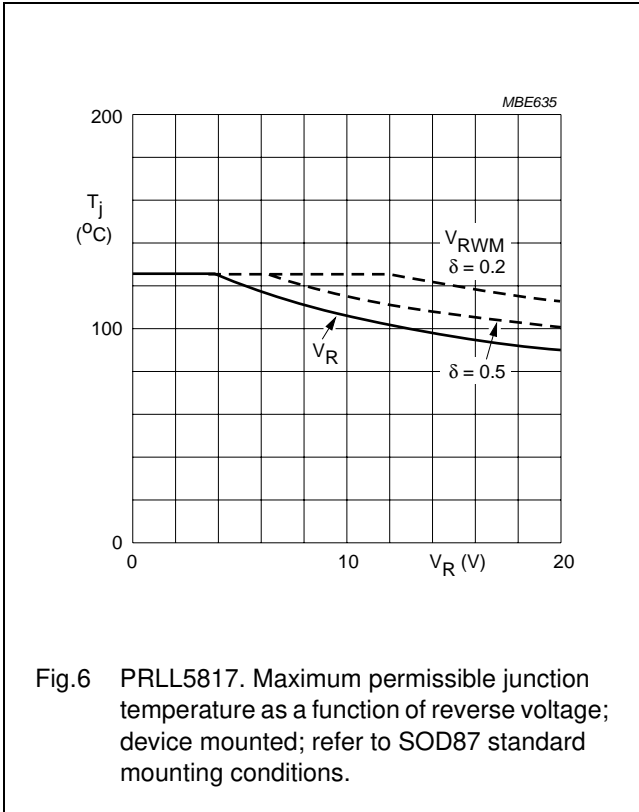


Fig.5 PRLL5819. Maximum values steady state forward power dissipation as a function of the average forward current;  $a = I_{F(RMS)}/I_{F(AV)}$ .

Schottky barrier diodes

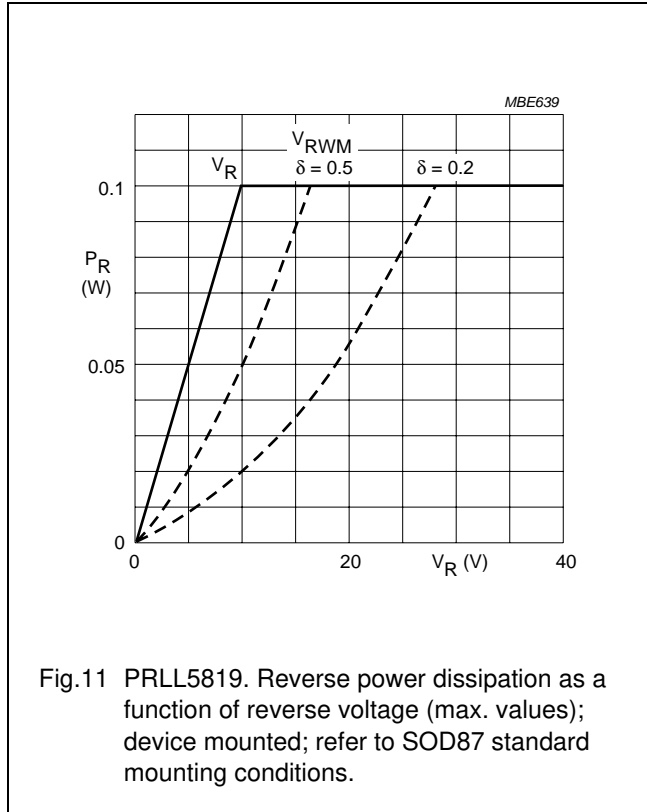
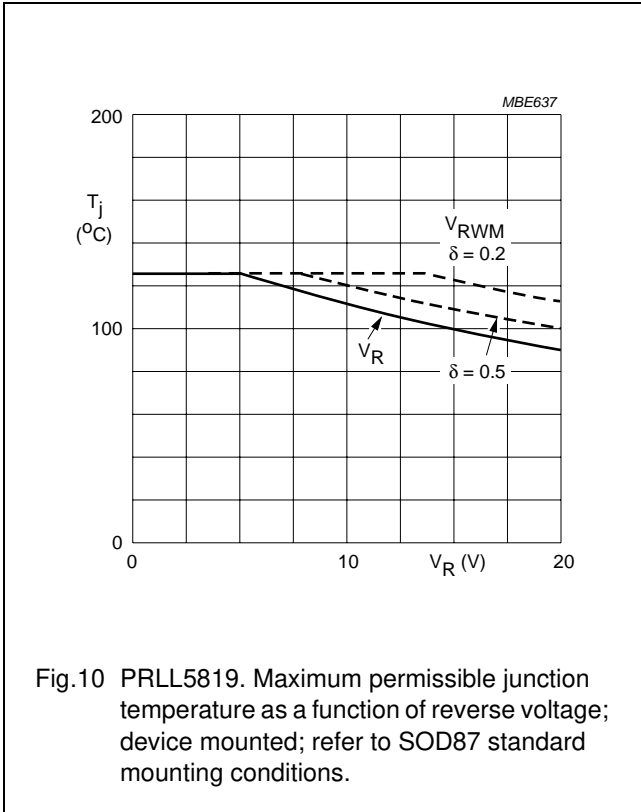
PRLL5817; PRLL5818;  
PRLL5819





Schottky barrier diodes

PRL5817; PRL5818;  
PRL5819



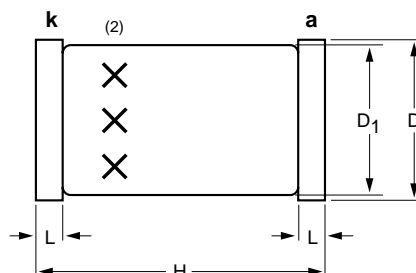
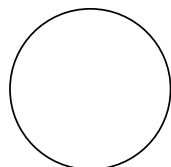
Schottky barrier diodes

PRL5817; PRL5818;  
PRL5819

PACKAGE OUTLINE

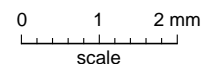
Hermetically sealed glass surface mounted package;  
Implotec™(1) technology; 2 connectors

SOD87



DIMENSIONS (mm are the original dimensions)

| UNIT | D          | D1         | H          | L   |
|------|------------|------------|------------|-----|
| mm   | 2.1<br>2.0 | 2.0<br>1.8 | 3.7<br>3.3 | 0.3 |



Notes

1. Implotec is a trademark of Philips.
2. The marking indicates the cathode.

| OUTLINE VERSION | REFERENCES |       |      |  | EUROPEAN PROJECTION | ISSUE DATE            |
|-----------------|------------|-------|------|--|---------------------|-----------------------|
|                 | IEC        | JEDEC | EIAJ |  |                     |                       |
| SOD87           | 100H03     |       |      |  |                     | 99-03-31-<br>99-06-04 |

## Schottky barrier diodes

PRL5817; PRL5818;  
PRL5819

## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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# ***NXP Semiconductors***

## **Customer notification**

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## **Contact information**

For additional information please visit: <http://www.nxp.com>

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